DATA SHEET

TDA8764
10-bit high-speed low-power ADC with internal reference regulator

Preliminary specification

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10-bit high-speed low-power ADC with internal reference regulator

TDA8764

FEATURES

- 10-bit resolution (binary or gray code)
- Sampling rate up to 40 MHz (/4 version)
  Sampling rate up to 80 MHz (/8 version)
- DC sampling allowed
- One clock cycle conversion only
- High signal-to-noise ratio over a large analog input frequency range (9.5 effective bits at 5 MHz; full-scale input at f_{clk} = 40 MHz)
- No missing codes guaranteed
- In-Range (IR) CMOS output
- TTL and CMOS levels compatible digital inputs
- 2.7 to 3.6 V CMOS digital outputs
- Low-level AC clock input signal allowed
- Internal reference voltage regulator
- Power dissipation only 250 mW (typical for /4 version)
  Power dissipation only 375 mW (typical for /8 version)
- Low analog input capacitance, no buffer amplifier required
- No sample-and-hold circuit required.

APPLICATIONS

High-speed analog-to-digital conversion for:

- Video data digitizing
- Radar pulse analysis
- Transient signal analysis
- High energy physics research
- $\Sigma\Delta$ modulators
- Medical imaging.

GENERAL DESCRIPTION

The TDA8764 is a 10-bit high-speed low-power Analog-to-Digital Converter (ADC) for professional video and other applications. It converts the analog input signal into 10-bit binary or gray coded digital words at a maximum sampling rate of 40 MHz (/4 version) and 80 MHz (/8 version). All digital inputs and outputs are TTL compatible, although a low-level sine wave clock input signal is allowed.

The device includes an internal voltage reference regulator.

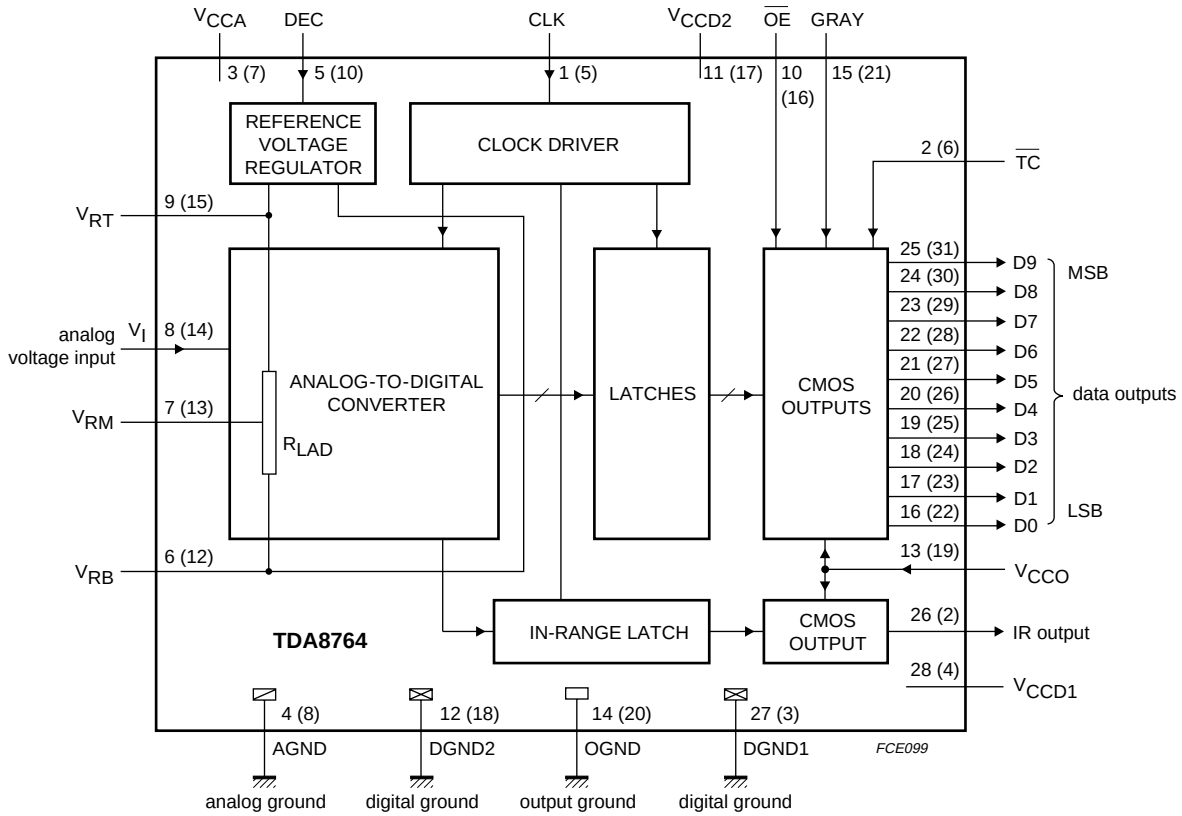
ORDERING INFORMATION

TYPE NUMBER	PACKAGE			SAMPLING FREQUENCY (MHz)
	NAME	DESCRIPTION	VERSION	
TDA8764TS/4	SSOP28	plastic shrink small outline package; 28 leads; body width 5.3 mm	SOT341-1	40
TDA8764TS/8				80
TDA8764HL/4	LQFP32	plastic low profile quad flat package; 32 leads; body 5 × 5 × 1.4 mm	SOT401-1	40
TDA8764HL/8				80

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CCA}	analog supply voltage		4.75	5.0	5.25	V
V_{CCD}	digital supply voltage		4.75	5.0	5.25	V
V_{CCO}	output stages supply voltage		2.7	3.3	3.6	V
I_{CCA}	analog supply current					
	TDA8764TS/4; TDA8764HL/4		–	25	tbf	mA
	TDA8764TS/8; TDA8764HL/8		–	45	tbf	mA
I_{CCD}	digital supply current					
	TDA8764TS/4; TDA8764HL/4		–	25	tbf	mA
	TDA8764TS/8; TDA8764HL/8		–	30	tbf	mA
I_{CCO}	output stages supply current					
	TDA8764TS/4; TDA8764HL/4	f_{clk} = 40 MHz; ramp input	–	0	tbf	mA
	TDA8764TS/8; TDA8764HL/8	f_{clk} = 80 MHz; ramp input	–	0	tbf	mA
INL	integral non-linearity					
	TDA8764TS/4; TDA8764HL/4	f_{clk} = 40 MHz; ramp input	–	±0.8	tbf	LSB
	TDA8764TS/8; TDA8764HL/8	f_{clk} = 80 MHz; ramp input	–	±0.8	tbf	LSB
DNL	differential non-linearity					
	TDA8764TS/4; TDA8764HL/4	f_{clk} = 40 MHz; ramp input	–	±0.25	tbf	LSB
	TDA8764TS/8; TDA8764HL/8	f_{clk} = 80 MHz; ramp input	–	±0.25	tbf	LSB
$f_{clk(max)}$	maximum clock frequency					
	TDA8764TS/4; TDA8764HL/4		40	–	–	MHz
	TDA8764TS/8; TDA8764HL/8		80	–	–	MHz
P_{tot}	total power dissipation					
	TDA8764TS/4; TDA8764HL/4	f_{clk} = 40 MHz; ramp input	–	250	tbf	mW
	TDA8764TS/8; TDA8764HL/8	f_{clk} = 80 MHz; ramp input	–	375	tbf	mW

BLOCK DIAGRAM



The pin numbers given in parenthesis refer to the LQFP32 package.

Fig.1 Block diagram.

PINNING

SYMBOL	PINS		DESCRIPTION
	SSOP28	LQFP32	
CLK	1	5	clock input
$\overline{TC}$	2	6	twos complement input (input active LOW)
V_{CCA}	3	7	analog supply voltage (+5 V)
AGND	4	8	analog ground
DEC	5	10	decoupling input
V_{RB}	6	12	reference voltage BOTTOM input
V_{RM}	7	13	reference voltage MIDDLE input
V_I	8	14	analog input voltage
V_{RT}	9	15	reference voltage TOP input
$\overline{OE}$	10	16	output enable input (input active LOW)
V_{CCD2}	11	17	digital supply voltage 2 (+5 V)
DGND2	12	18	digital ground 2
V_{CCO}	13	19	supply voltage for output stages (2.7 to 3.6 V)
OGND	14	20	output ground
GRAY	15	21	gray code input (input active HIGH)
D0	16	22	data output; bit 0 (LSB)
D1	17	23	data output; bit 1
D2	18	24	data output; bit 2
D3	19	25	data output; bit 3
D4	20	26	data output; bit 4
D5	21	27	data output; bit 5
D6	22	28	data output; bit 6
D7	23	29	data output; bit 7
D8	24	30	data output; bit 8
D9	25	31	data output; bit 9 (MSB)
IR	26	2	in-range data output
DGND1	27	3	digital ground 1
V_{CCD1}	28	4	digital supply voltage 1 (+5 V)
n.c.	–	1, 9, 11 and 32	not connected

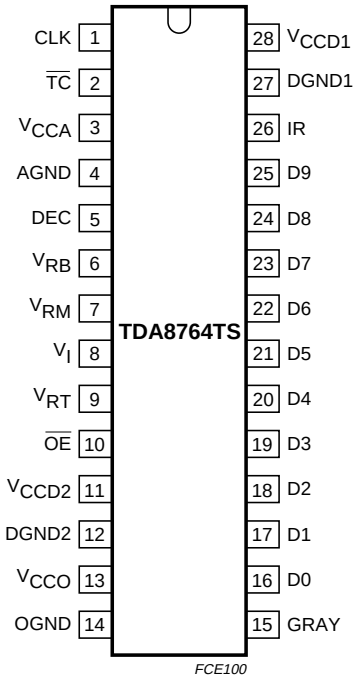


Fig.2 Pin configuration (SSOP28).

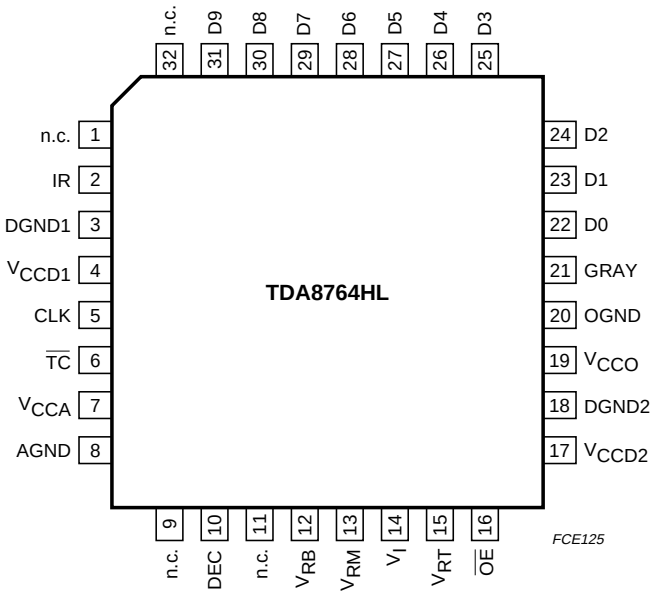


Fig.3 Pin configuration (LQFP32).

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CCA}	analog supply voltage	note 1	–0.3	+7.0	V
V_{CCD}	digital supply voltage	note 1	–0.3	+7.0	V
V_{CCO}	output stages supply voltage	note 1	–0.3	+7.0	V
ΔV_{CC}	supply voltage difference				
	$V_{CCA} - V_{CCD}$		–1.0	+1.0	V
	$V_{CCA} - V_{CCO}$		–1.0	+4.0	V
	$V_{CCD} - V_{CCO}$		–1.0	+4.0	V
V_I	input voltage	referenced to AGND	–0.3	+7.0	V
$V_{i(sw)(p-p)}$	AC input voltage for switching (peak-to-peak value)	referenced to DGND	–	V_{CCD}	V
I_O	output current		–	10	mA
T_{stg}	storage temperature		–55	+150	°C
T_{amb}	operating ambient temperature		–40	+85	°C
T_j	junction temperature		–	150	°C

Note

1. The supply voltages V_{CCA}, V_{CCD} and V_{CCO} may have any value between –0.3 V and +7.0 V provided that the supply voltage differences ΔV_{CC} are respected.

HANDLING

Inputs and outputs are protected against electrostatic discharges in normal handling. However, to be totally safe, it is desirable to take normal precautions appropriate to handling integrated circuits.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		
	SSOP28		110	K/W
	LQFP32		90	K/W

CHARACTERISTICS

The characteristics given refer to the SSOP28 package. $V_{CCA} = V_3$ to V_4 = 4.75 to 5.25 V; $V_{CCD} = V_{11}$ to V_{12} and V_{28} to V_{27} = 4.75 to 5.25 V; $V_{CCO} = V_{13}$ to V_{14} = 2.7 to 3.6 V; AGND and DGND shorted together; T_{amb} = 0 to 70 °C; typical values measured at $V_{CCA} = V_{CCD}$ = 5 V and V_{CCO} = 3.3 V; C_L = 10 pF and T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Supplies						
V_{CCA}	analog supply voltage		4.75	5.0	5.25	V
V_{CCD1}	digital supply voltage 1		4.75	5.0	5.25	V
V_{CCD2}	digital supply voltage 2		4.75	5.0	5.25	V
V_{CCO}	output stages supply voltage		2.7	3.3	3.6	V
ΔV_{CC}	supply voltage difference					
	$V_{CCA} - V_{CCD}$		–0.20	–	+0.20	V
	$V_{CCA} - V_{CCO}$		–0.20	–	+2.55	V
	$V_{CCD} - V_{CCO}$		–0.20	–	+2.55	V
I_{CCA}	analog supply current					
	TDA8764TS/4; TDA8764HL/4		–	25	tbf	mA
	TDA8764TS/8; TDA8764HL/8		–	45	tbf	mA
I_{CCD}	digital supply current					
	TDA8764TS/4; TDA8764HL/4		–	25	tbf	mA
	TDA8764TS/8; TDA8764HL/8		–	30	tbf	mA
I_{CCO}	output stages supply current					
	TDA8764TS/4; TDA8764HL/4	f_{clk} = 40 MHz; ramp input	–	0	tbf	mA
	TDA8764TS/8; TDA8764HL/8	f_{clk} = 80 MHz; ramp input	–	0	tbf	mA
Inputs						
CLOCK INPUT; CLK (REFERENCED TO DGND); note 1						
V_{IL}	LOW-level input voltage		0	–	0.8	V
V_{IH}	HIGH-level input voltage		2	–	V_{CCD}	V
I_{IL}	LOW-level input current	V_{CLK} = 0.8 V	–1	0	+1	µA
I_{IH}	HIGH-level input current	V_{CLK} = 2 V	–	2	10	µA
C_i	input capacitance		–	2	–	pF
INPUTS $\overline{OE}$, $\overline{TC}$ AND GRAY (REFERENCED TO DGND); see Tables 3 and 4						
V_{IL}	LOW-level input voltage		0	–	0.8	V
V_{IH}	HIGH-level input voltage		2	–	V_{CCD}	V
I_{IL}	LOW-level input current	V_{IL} = 0.8 V	–1	–	–	µA
I_{IH}	HIGH-level input current	V_{IH} = 2 V	–	–	1	µA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_I (ANALOG INPUT VOLTAGE REFERENCED TO AGND)						
I_{IL}	LOW-level input current					
	TDA8764TS/4; TDA8764HL/4	$V_I = V_{RB}$	–	0	–	μA
	TDA8764TS/8; TDA8764HL/8	$V_I = V_{RB}$	–	0	–	μA
I_{IH}	HIGH-level input current					
	TDA8764TS/4; TDA8764HL/4	$V_I = V_{RT}$	–	45	–	μA
	TDA8764TS/8; TDA8764HL/8	$V_I = V_{RT}$	–	85	–	μA
Y_i	input admittance TDA8764TS/4; TDA8764HL/4	f_i = 5 MHz; note 2				
	input resistance		–	70	–	kΩ
	input capacitance		3	5	7	pF
	input admittance TDA8764TS/8; TDA8764HL/8	f_i = 5 MHz; note 2				
	input resistance		–	45	–	kΩ
	input capacitance		3	5	7	pF
Reference voltages for the resistor ladder using the internal voltage regulator; see Table 1						
V_{RB}	reference voltage BOTTOM		tbf	1.3	tbf	V
V_{RT}	reference voltage TOP		tbf	3.7	tbf	V
$V_{diff(ref)}$	differential reference voltage $V_{RT} - V_{RB}$		tbf	2.4	tbf	V
TC_{Vdiff}	temperature coefficient of differential reference voltage		–	tbf	–	mV/K
$V_{offset(B)}$	offset voltage BOTTOM	note 3	–	161	–	mV
$V_{offset(T)}$	offset voltage TOP	note 3	–	161	–	mV
$V_{I(p-p)}$	analog input voltage (peak-to-peak value)	note 4	tbf	2.08	tbf	V
Outputs						
DIGITAL OUTPUTS D9 TO D0 AND IR (REFERENCED TO OGND)						
V_{OL}	LOW-level output voltage					
	TDA8764TS/4; TDA8764HL/4	I_{OL} = 1 mA	0	–	0.5	V
	TDA8764TS/8; TDA8764HL/8	I_{OL} = 2 mA	0	–	0.5	V
V_{OH}	HIGH-level output voltage					
	TDA8764TS/4; TDA8764HL/4	I_{OH} = –1 mA	$V_{CCO} - 0.5$	–	V_{CCO}	V
	TDA8764TS/8; TDA8764HL/8	I_{OH} = –2 mA	$V_{CCO} - 0.5$	–	V_{CCO}	V
I_{OZ}	output current in 3-state mode	$0.5\ V < V_o < V_{CCO}$	–20	–	+20	μA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Switching characteristics						
CLOCK INPUT; CLK; see Fig.5; note 1						
$f_{clk(max)}$	maximum clock frequency					
	TDA8764TS/4; TDA8764HL/4		40	–	–	MHz
	TDA8764TS/8; TDA8764HL/8		80	–	–	MHz
t_{CPH}	clock pulse width HIGH					
	TDA8764TS/4; TDA8764HL/4		7	–	–	ns
	TDA8764TS/8; TDA8764HL/8		5	–	–	ns
t_{CPL}	clock pulse width LOW					
	TDA8764TS/4; TDA8764HL/4		7	–	–	ns
	TDA8764TS/8; TDA8764HL/8		5	–	–	ns
Analog signal processing						
LINEARITY						
INL	integral non-linearity					
	TDA8764TS/4; TDA8764HL/4	f_{clk} = 40 MHz; ramp input	–	±0.8	tbf	LSB
	TDA8764TS/8; TDA8764HL/8	f_{clk} = 80 MHz; ramp input	–	±0.8	tbf	LSB
DNL	differential non-linearity					
	TDA8764TS/4; TDA8764HL/4	f_{clk} = 40 MHz; ramp input	–	±0.25	tbf	LSB
	TDA8764TS/8; TDA8764HL/8	f_{clk} = 80 MHz; ramp input	–	±0.25	tbf	LSB
E_{offset}	offset error	middle code	–	±1	–	LSB
E_G	gain error (from device to device) using internal reference voltage	note 5	–	tbf	–	%
BANDWIDTH (f_{clk} = 40 MHz)/4 VERSION;						
B	analog bandwidth	full-scale sine wave; note 6	–	20	–	MHz
		75% full-scale sine wave; note 6	–	30	–	MHz
		small signal at mid-scale; V_I = ±10 LSB at code 512; note 6	–	350	–	MHz
t_{stLH}	analog input settling time LOW-to-HIGH	full-scale square wave; see Fig.7 and note 7	–	tbf	tbf	ns
t_{stHL}	analog input settling time HIGH-to-LOW	full-scale square wave; see Fig.7 and note 7	–	tbf	tbf	ns

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BANDWIDTH (f_{clk} = 80 MHz) /8 VERSION;						
B	analog bandwidth	full-scale sine wave; note 6	–	40	–	MHz
		75% full-scale sine wave; note 6	–	60	–	MHz
		small signal at mid-scale; V_i = ±10 LSB at code 512; note 6	–	700	–	MHz
t_{stLH}	analog input settling time LOW-to-HIGH	full-scale square wave; see Fig.7 and note 7	–	tbf	tbf	ns
t_{stHL}	analog input settling time HIGH-to-LOW	full-scale square wave; see Fig.7 and note 7	–	tbf	tbf	ns
HARMONICS (f_{clk} = 40 MHz) /4 VERSION;						
$H_{all(FS)}$	harmonics (full-scale); all components	f_i = 5 MHz				
	second harmonics		–	–70	tbf	dBc
	third harmonics		–	–90	tbf	dBc
SFDR	spurious free dynamic range	f_i = 5 MHz	–	tbf	–	dBc
THD	total harmonic distortion	f_i = 5 MHz	–	–70	–	dB
HARMONICS (f_{clk} = 80 MHz)/8 VERSION;						
$H_{all(FS)}$	harmonics (full-scale); all components	f_i = 5 MHz				
	second harmonics		–	–71	tbf	dBc
	third harmonics		–	–87	tbf	dBc
SFDR	spurious free dynamic range	f_i = 5 MHz	–	tbf	–	dBc
THD	total harmonic distortion	f_i = 5 MHz	–	–70	–	dB
SIGNAL-TO-NOISE RATIO; note 8						
$SNR_{(FS)}$	signal-to-noise ratio (full-scale)	without harmonics; f_i = 5 MHz				
		f_{clk} = 40 MHz; /4 version	tbf	58	–	dB
		f_{clk} = 80 MHz; /8 version	tbf	58	–	dB
EFFECTIVE BITS; note 8						
EB	effective bits TDA8764TS/4; TDA8764HL/4	f_{clk} = 40 MHz				
		f_i = 5 MHz	tbf	9.5	tbf	bits
		f_i = 7.5 MHz	tbf	9.2	tbf	bits
		f_i = 10 MHz	tbf	9.0	tbf	bits
		f_i = 20 MHz	tbf	tbf	tbf	bits
	effective bits TDA8764TS/8; TDA8764HL/8	f_{clk} = 80 MHz				
		f_i = 5 MHz	tbf	9.5	tbf	bits
		f_i = 10 MHz	tbf	tbf	tbf	bits
		f_i = 20 MHz	tbf	tbf	tbf	bits
		f_i = 40 MHz	tbf	tbf	tbf	bits

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
TWO-TONE; note 9						
TTID	two-tone intermodulation distortion	f_{clk} = 40 MHz	–	tbf	–	dB
		f_{clk} = 80 MHz	–	tbf	–	dB
BIT ERROR RATE						
BER	bit error rate	f_i = 5 MHz; V_i = ±16 LSB at code 512				
		f_{clk} = 40 MHz	–	10^{-13}	–	times/ sample
		f_{clk} = 80 MHz	–	10^{-13}	–	times/ sample
Timing (f_{clk} = 40 MHz; C_L = 10 pF) /4 version; see Fig.5 and note 10						
t_{ds}	sampling delay time		–	–	2	ns
t_h	output hold time		5	–	–	ns
t_d	output delay time	V_{CCO} = 2.7 V	tbf	12	tbf	ns
		V_{CCO} = 3.3 V	tbf	11	tbf	ns
C_L	digital output load capacitance		–	–	10	pF
SR	slew rate	V_{CCO} = 2.7 V; C_L = 10 pF	–	–	tbf	V/µs
Timing (f_{clk} = 80 MHz; C_L = 10 pF) /8 version; see Fig.5 and note 10						
t_{ds}	sampling delay time		–	–	2	ns
t_h	output hold time		4	–	–	ns
t_d	output delay time	V_{CCO} = 2.7 V	tbf	8	tbf	ns
		V_{CCO} = 3.3 V	tbf	7	tbf	ns
C_L	digital output load capacitance		–	–	10	pF
SR	slew rate	V_{CCO} = 2.7 V; C_L = 10 pF	–	–	tbf	V/µs
3-state output delay times (f_{clk} = 40 MHz) /4 version; see Fig.6						
t_{dZH}	enable HIGH		–	tbf	tbf	ns
t_{dZL}	enable LOW		–	tbf	tbf	ns
t_{dHZ}	disable HIGH		–	tbf	tbf	ns
t_{dLZ}	disable LOW		–	tbf	tbf	ns
3-state output delay times (f_{clk} = 80 MHz) /8 version; see Fig.6						
t_{dZH}	enable HIGH		–	tbf	tbf	ns
t_{dZL}	enable LOW		–	tbf	tbf	ns
t_{dHZ}	disable HIGH		–	tbf	tbf	ns
t_{dLZ}	disable LOW		–	tbf	tbf	ns

Notes

1. In addition to a good layout of the digital and analog ground, it is recommended that the rise and fall times of the clock must not be less than 0.5 ns.
2. The input admittance is $V_i = \left(\frac{1}{R_i} + Cijw\right)$
3. Analog input voltages producing code 0 up to and including code 1023:
   a) $V_{offset(B)}$ (offset voltage BOTTOM) is the difference between the analog input which produces data equal to 00 and the reference voltage BOTTOM (V_{RB}) at T_{amb} = 25 °C.
   b) $V_{offset(T)}$ (offset voltage TOP) is the difference between reference voltage TOP (V_{RT}) and the analog input which produces data outputs equal to code 1023 at T_{amb} = 25 °C.
4. In order to ensure the optimum linearity performance of such converter architecture the lower and upper extremities of the converter reference resistor ladder (corresponding to output codes 0 and 1023 respectively) are connected to pins V_{RB} and V_{RT} via offset resistors R_{OB} and R_{OT} as shown in Fig.4.
   a) The current flowing into the resistor ladder is $I_L = \frac{V_{RT} - V_{RB}}{R_{OB} + R_L + R_{OT}}$ and the full-scale input range at the converter, to cover code 0 to code 1023, is $V_I = R_L \times I_L = \frac{R_L}{R_{OB} + R_L + R_{OT}} \times (V_{RT} - V_{RB}) = 0.866 \times (V_{RT} - V_{RB})$
   b) Since R_L, R_{OB} and R_{OT} have similar behaviour with respect to process and temperature variation, the ratio $\frac{R_L}{R_{OB} + R_L + R_{OT}}$ will be kept reasonably constant from device to device. Consequently variation of the output codes at a given input voltage depends mainly on the difference $V_{RT} - V_{RB}$ and its variation with temperature and supply voltage. When several ADCs are connected in parallel and fed with the same reference source, the matching between each of them is then optimized.
5. $E_G = \frac{(V_{1023} - V_0) - V_{i(p-p)}}{V_{i(p-p)}} \times 100$
6. The analog bandwidth is defined as the maximum input sine wave frequency which can be applied to the device. No glitches greater than 2 LSBs, nor any significant attenuation are observed in the reconstructed signal.
7. The analog input settling time is the minimum time required for the input signal to be stabilized after a sharp full-scale input (square wave signal) in order to sample the signal and obtain correct output data.
8. Effective bits are obtained via a Fast Fourier Transform (FFT) treatment taking 8 K acquisition points per equivalent fundamental period. The calculation takes into account all harmonics and noise up to half of the clock frequency (NYQUIST frequency). Conversion to signal-to-noise ratio: SINAD = EB × 6.02 + 1.76 dB.
9. Intermodulation measured relative to either tone with analog input frequencies of 5 and 5.1 MHz. The two input signals have the same amplitude and the total amplitude of both signals provides full-scale to the converter.
10. Output data acquisition: the output data is available after the maximum delay time of $t_{d(max)}$. For the 80 MHz version it is recommended to have the lowest possible output load.

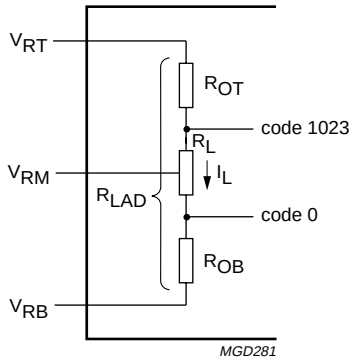


Fig.4 Explanation of note 4.

Table 1 Output coding and input voltage (typical values; referenced to AGND); binary and gray codes

STEP	$V_{i(p-p)}$	IR	BINARY OUTPUT BITS										GRAY OUTPUT BITS									
			D9	D8	D7	D6	D5	D4	D3	D2	D1	D0	D9	D8	D7	D6	D5	D4	D3	D2	D1	D0
U/F	<tbf	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
0	tbf	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
1	...	1	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	0	0	0	0	1
...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...
...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...
1022	...	1	1	1	1	1	1	1	1	1	1	0	1	0	0	0	0	0	0	0	0	1
1023	tbf	1	1	1	1	1	1	1	1	1	1	1	1	0	0	0	0	0	0	0	0	0
O/F	>tbf	0	1	1	1	1	1	1	1	1	1	1	1	0	0	0	0	0	0	0	0	0

Table 2 Output coding and input voltage (typical values; referenced to AGND); binary and twos complement codes

STEP	$V_{i(p-p)}$	IR	BINARY OUTPUT BITS										TWO'S COMPLEMENT OUTPUT BITS									
			D9	D8	D7	D6	D5	D4	D3	D2	D1	D0	D9	D8	D7	D6	D5	D4	D3	D2	D1	D0
U/F	<tbf	0	0	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	0	0	0	0
0	tbf	1	0	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	0	0	0	0
1	...	1	0	0	0	0	0	0	0	0	0	1	1	0	0	0	0	0	0	0	0	1
...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...
...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...	...
1022	...	1	1	1	1	1	1	1	1	1	1	0	0	1	1	1	1	1	1	1	1	0
1023	tbf	1	1	1	1	1	1	1	1	1	1	1	0	1	1	1	1	1	1	1	1	1
O/F	>tbf	0	1	1	1	1	1	1	1	1	1	1	0	1	1	1	1	1	1	1	1	1

Table 3 Mode selection

$\overline{TC}$	$\overline{OE}$	D9 TO D0	IR
X	1	high impedance	high impedance
0	0	active; two complement	active
1	0	active; binary	active

Table 4 Mode selection

$\overline{GRAY}$	$\overline{OE}$	D9 TO D0	IR
X	1	high impedance	high impedance
0	0	active; binary	active
1	0	active; gray	active

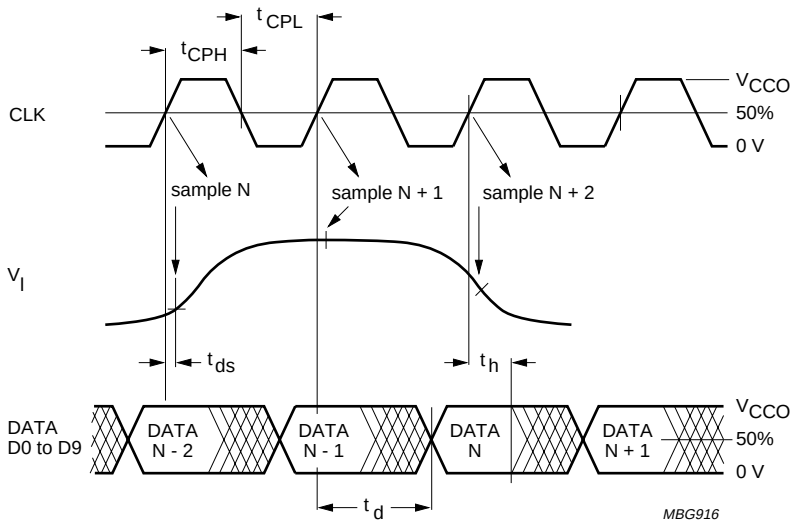
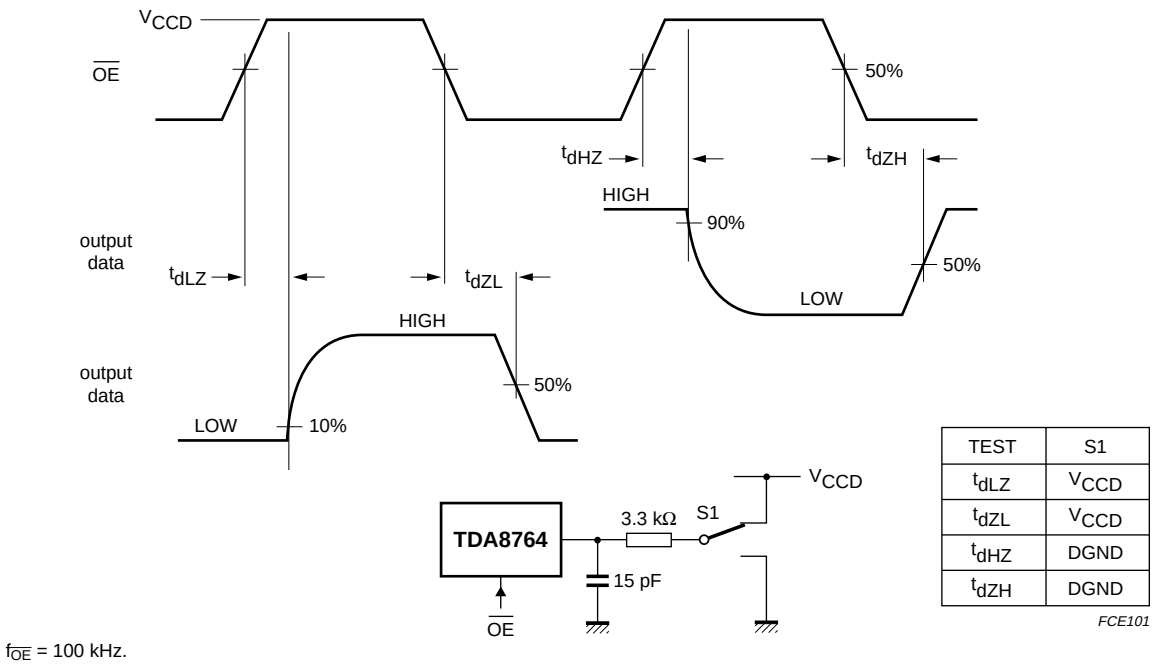


Fig.5 Timing diagram.



$f_{\overline{OE}}$ = 100 kHz.

Fig.6 Timing diagram and test conditions of 3-state output delay time.

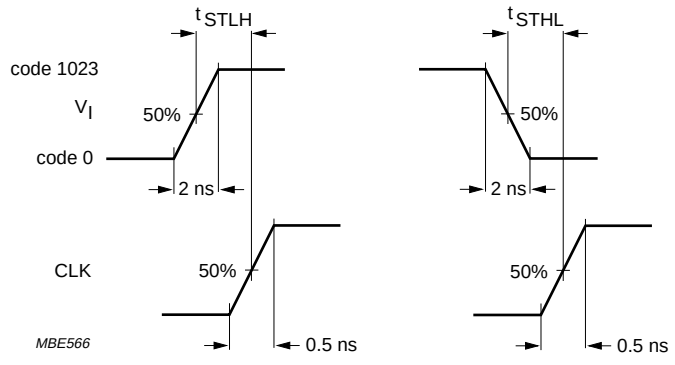


Fig.7 Analog input settling time diagram.

INTERNAL PIN CONFIGURATIONS

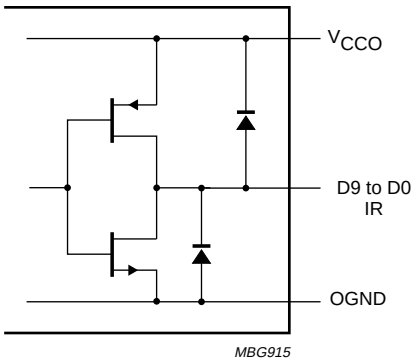


Fig.8 CMOS data and in range outputs.

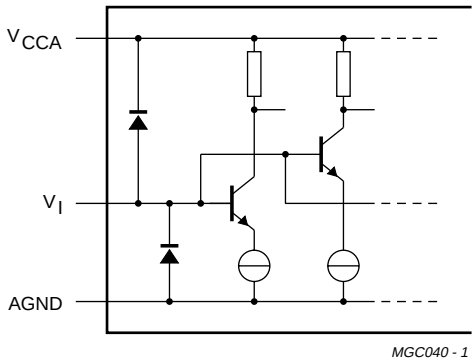


Fig.9 Analog inputs.

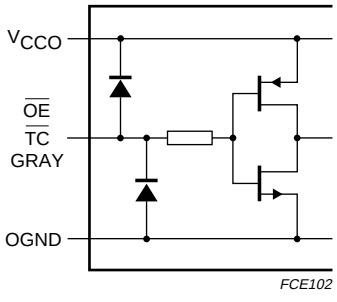


Fig.10 $\overline{OE}$, GRAY and $\overline{TC}$ inputs.

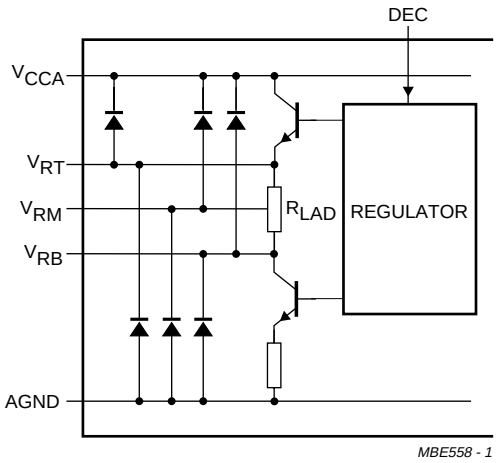


Fig.11 V_{RB}, V_{RM} and V_{RT}.

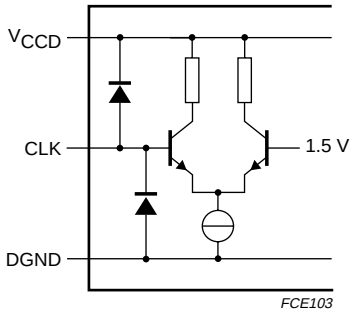
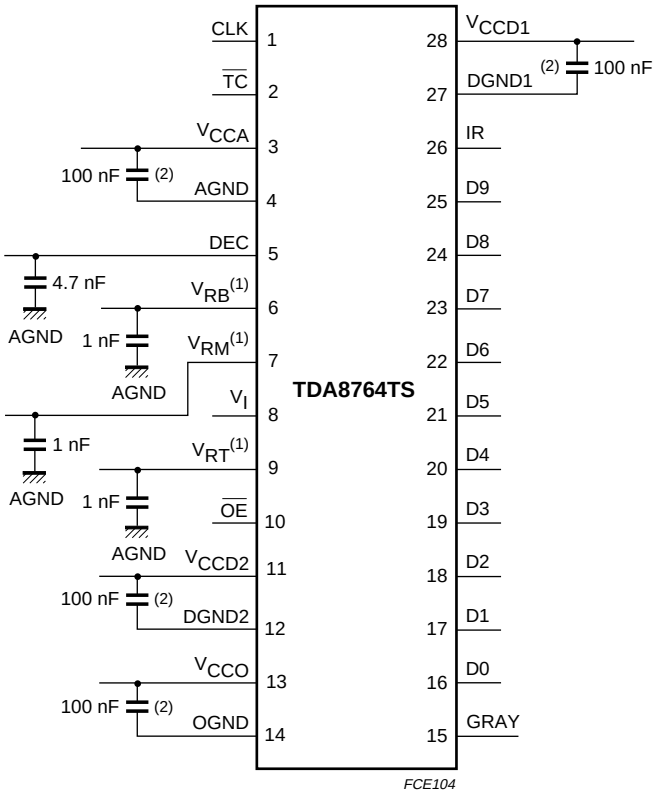


Fig.12 CLK input.

APPLICATION INFORMATION



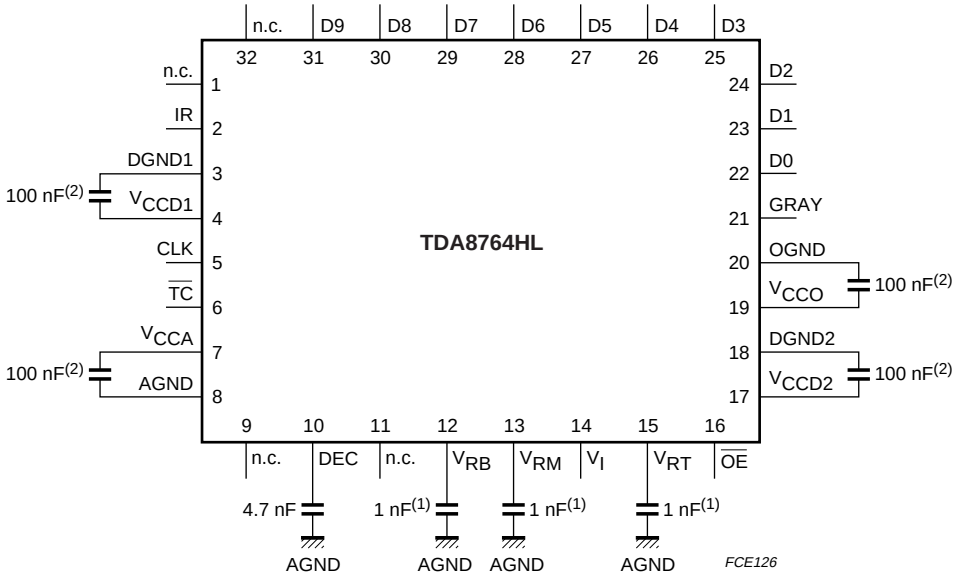
The analog and digital supplies should be separated and well decoupled.

An application note is available which describes the design and the realization of a demonstration board that uses TDA8764HL in an application environment.

(1) V_{RB}, V_{RM} and V_{RT} are decoupled to AGND.

(2) Decoupling capacitor for supplies; **it must be placed close to the device**.

Fig.13 Application diagram (SSOP28).



The analog and digital supplies should be separated and well decoupled.

An application note is available which describes the design and the realization of a demonstration board that uses TDA8764HL in an application environment.

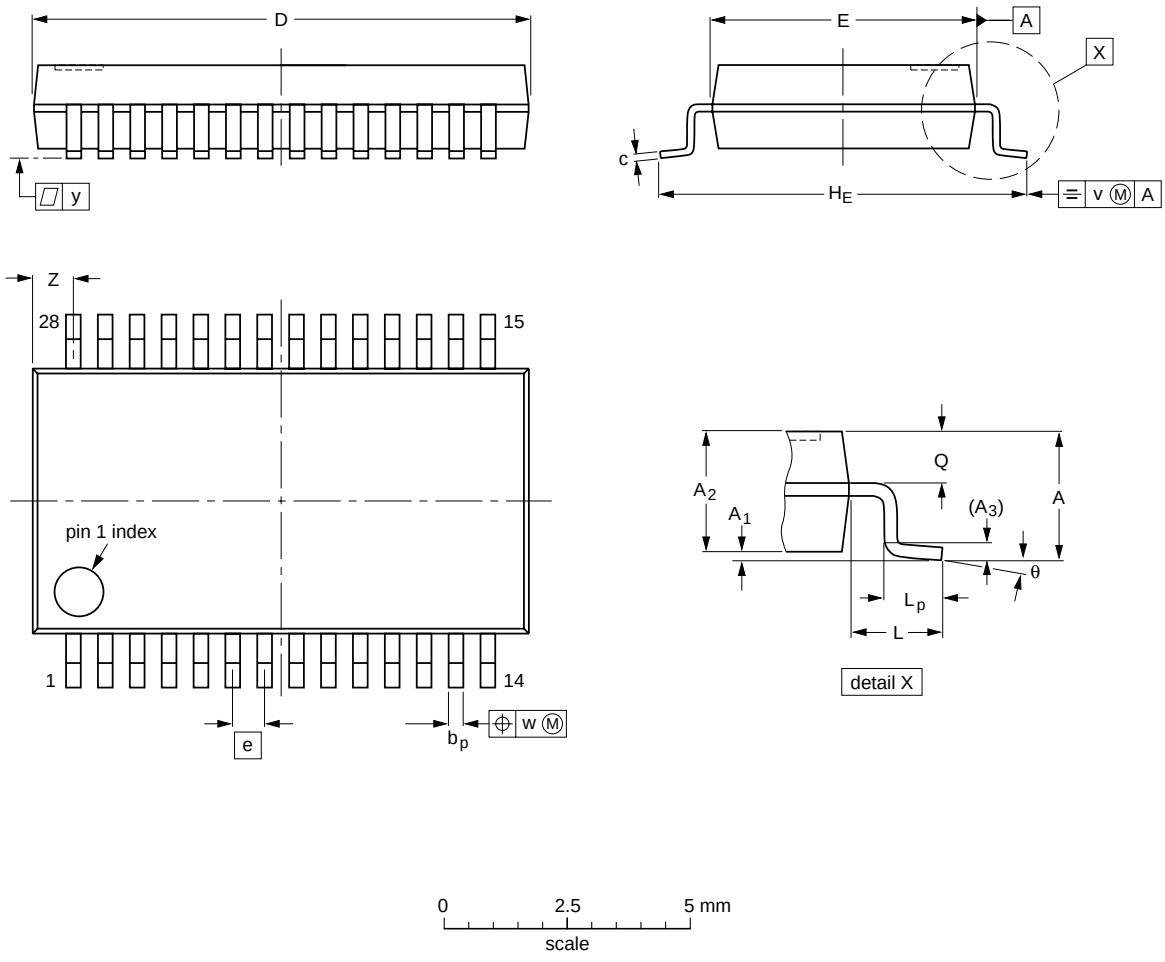
(1) V_{RB}, V_{RM} and V_{RT} are decoupled to AGND.

(2) Decoupling capacitor for supplies; **it must be placed close to the device**.

Fig.14 Application diagram (LQFP32).

PACKAGE OUTLINES

SSOP28: plastic shrink small outline package; 28 leads; body width 5.3 mm **SOT341-1**



DIMENSIONS (mm are the original dimensions)

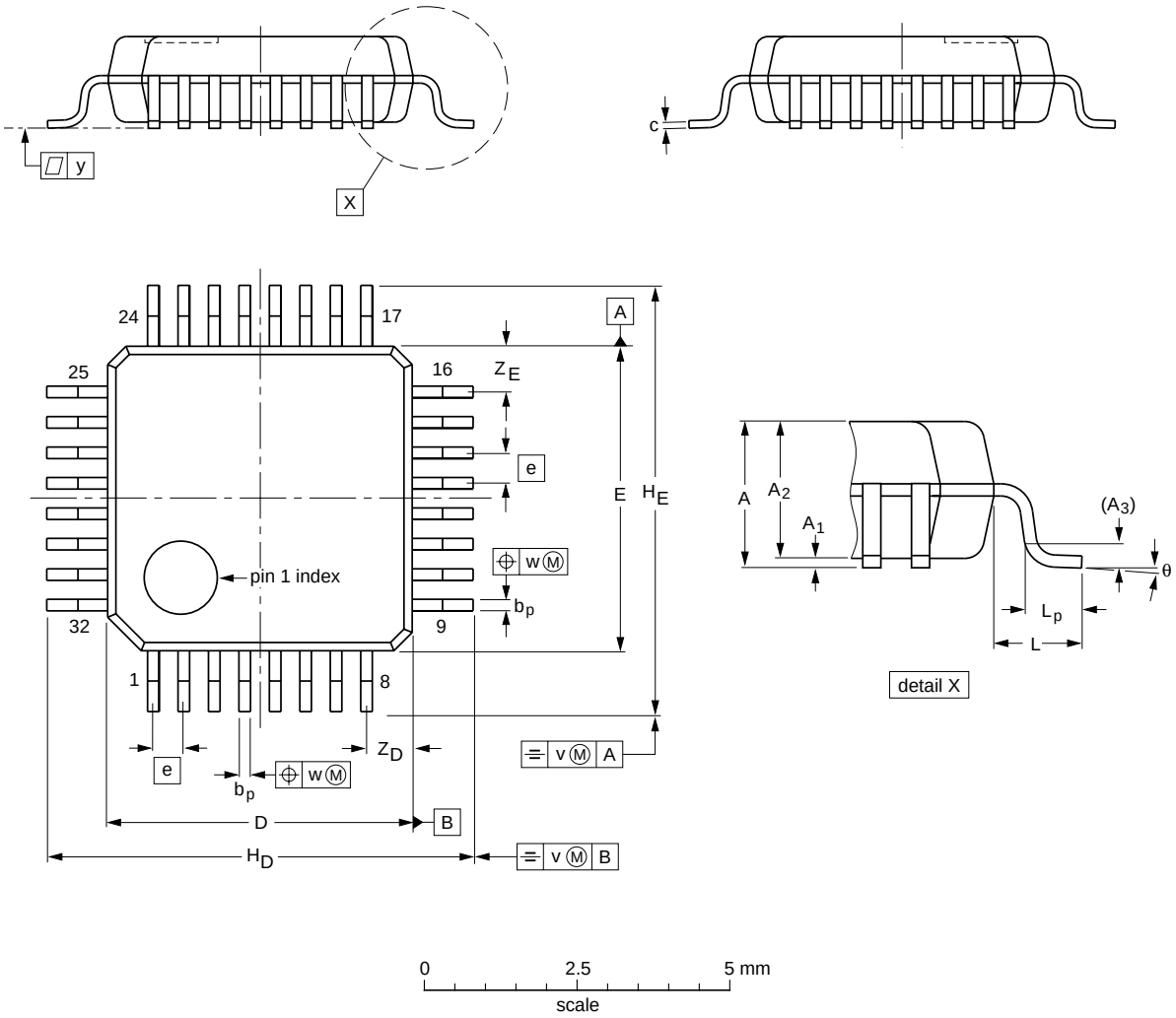
UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	10.4 10.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.1 0.7	8^o 0^o

Note

1. Plastic or metal protrusions of 0.20 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT341-1		MO-150AH				~~93-09-08~~ 95-02-04

LQFP32: plastic low profile quad flat package; 32 leads; body 5 x 5 x 1.4 mm **SOT401-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_D	H_E	L	L_p	v	w	y	$Z_D^{(1)}$	$Z_E^{(1)}$	θ
mm	1.60	0.15 0.05	1.5 1.3	0.25	0.27 0.17	0.18 0.12	5.1 4.9	5.1 4.9	0.5	7.15 6.85	7.15 6.85	1.0	0.75 0.45	0.2	0.12	0.1	0.95 0.55	0.95 0.55	7^o 0^o

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT401-1						~~95-12-19~~ 97-08-04

SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 230 °C.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
  - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
  - smaller than 1.27 mm, the footprint longitudinal axis **must** be parallel to the transport direction of the printed-circuit board.

  The footprint must incorporate solder thieves at the downstream end.
- For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C.
A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE	SOLDERING METHOD	
	WAVE	REFLOW(1)
BGA, SQFP	not suitable	suitable
HLQFP, HSQFP, HSOP, SMS	not suitable(2)	suitable
PLCC(3), SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended(3)(4)	suitable
SSOP, TSSOP, VSO	not recommended(5)	suitable

Notes

1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the *"Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods"*.
2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
3. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
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Where application information is given, it is advisory and does not form part of the specification.	

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